

09/605293

**FACSIMILE COVER SHEET**

**TO: Examiner N. Drew Richards, Art Unit 2815**

Company: Assistant Commissioner for Patents  
Fax No.: 703/872-9319

**FROM: Julie G. Cope, Reg. No. 48,624/amm**

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Patents, Trademarks and Related Matters

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Remarks:

**U.S. Patent Application Serial No. 09/605,293**

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## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of

Applicant : David L. Chapek  
Serial No. : 09/605,293  
Filed : June 28, 2000  
Title : SEMICONDUCTOR DEVICES INCLUDING A LAYER OF  
POLYCRYSTALLINE SILICON HAVING A SMOOTH  
MORPHOLOGY  
Docket : MIO 0037 VA  
Art Unit : 2815

Assistant Commissioner for Patents  
Washington, DC 20231  
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Sir:

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Julie G. Cope

Reg. No. 48,624

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AMENDMENT AFTER FINAL

This paper is being filed in response to the Office Action mailed on December 16, 2002. Entry of this amendment is requested as it is believed the amendments and remarks place the application in condition for allowance or will at least reduce the number of issues for appeal.

CLEAN VERSION OF THE AMENDMENTS

A version of the amendments showing the markings is provided in a separate appendix attached to this paper.

In the Specification

At page 8, lines 2-13 should read:

With continued reference to Fig. 1, the layer 14 of silicon dioxide 16 is formed on the substrate 12 by an conventional oxidation process or deposition process, and has been doped with hydrogen ions to provide a surface conducive to the deposition of polycrystalline silicon. Depending upon the nature of the layer 14 of silicon dioxide 16, the layer 14 of silicon dioxide 16 can be formed by thermal oxidation, chemical vapor deposition (CVD), low pressure chemical vapor deposition (LPCVD), plasma enhanced